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# **Kinetic Processes**

Crystal Growth, Diffusion, and Phase Transitions in Materials



WILEY-VCH Verlag GmbH & Co. KGaA

## Contents

### Preface *XIII*

<b>1</b>	<b>Introduction</b>	1
1.1	Arrhenius Plot	1
1.2	The Relationship between Kinetics and Thermodynamics	2
1.3	The Boltzmann Distribution	4
1.4	Kinetic Theory of Gases	6
1.5	Collisions	7
<b>2</b>	<b>Diffusion in Fluids</b>	11
2.1	Diffusion in a Gas	11
2.2	Diffusion in Liquids	12
2.2.1	Diffusion Distances	13
2.2.2	Molecular Dynamics Simulations of Diffusion in Liquids	13
2.2.3	Measurement of Diffusion Coefficients in Liquids	16
<b>3</b>	<b>Diffusion in Amorphous Materials</b>	19
3.1	Amorphous Materials	19
3.2	Network Glass Formers	20
3.2.1	Silica	20
3.2.2	Silicon and Germanium	20
3.3	The Glass Transition	22
3.4	The Free-Volume Model	23
3.5	Fictive Temperature	23
3.6	Diffusion in Polymers	24
3.7	The Stokes–Einstein Relationship	25
<b>4</b>	<b>Diffusion in Crystals</b>	27
4.1	Diffusion in a Crystal	27
4.2	Diffusion Mechanisms in Crystals	28
4.2.1	Vacancy Diffusion	28
4.2.2	Interstitial Diffusion	30

4.4	Equilibrium Concentration of Vacancies	30
4.4.1	Thermodynamic Analysis	30
4.4.2	Kinetic Analysis	32
4.5	Simmons and Balluffi Experiment	34
4.6	Ionic and Covalent Crystals	34
4.7	Stoichiometry	36
4.8	Measurement of Diffusion Coefficients	36
4.9	Surface Diffusion	37
4.10	Diffusion in Grain Boundaries	38
4.11	Kirkendall Effect	38
4.12	Whisker Growth	39
4.13	Electromigration	40
<b>5</b>	<b>Diffusion in Semiconductors</b>	<b>45</b>
5.1	Introduction	45
5.2.1	Vacancy Diffusion in Silicon	47
5.2.2	Diffusion of Phosphorus in Silicon	49
5.2.3	Diffusion of Arsenic in Silicon	50
5.2.4	Diffusion of Boron in Silicon	50
5.3	Diffusion of Zinc in GaAs	51
5.4	Recombination-enhanced Diffusion	52
5.5	Doping of Semiconductors	53
5.6	Point-Defect Generation in Silicon during Crystal Growth	53
5.7	Migration of Interstitials (and Liquid Droplets) in a Temperature Gradient	56
5.8	Oxygen in Silicon	57
5.9	Gettering	57
5.10	Solid-State Doping	58
<b>6</b>	<b>Ion Implantation</b>	<b>61</b>
6.1	Introduction	61
6.2	Ion Interactions	62
6.3	Implantation Damage	64
6.4	Rutherford Backscattering	67
6.5	Channeling	69
6.6	Silicon-on-Insulator	71
<b>7</b>	<b>Mathematics of Diffusion</b>	<b>75</b>
7.1	Random Walk	75
7.2	The Diffusion Equation	77
7.3	Solutions to the Diffusion Equation	79
7.3.1	Gaussian Concentration Distribution	79
7.3.2	Error Function Concentration Distribution	82
7.3.3	p/n Junction Depth	84
7.3.4	Separation of Variables	85

7.4	Numerical Methods	90
7.4.1	Finite Difference Method for Diffusion	91
7.4.2	Initial Surface Concentration Boundary Conditions	91
7.4.3	Implanted Concentration Profile	92
7.4.4	Zero Flux Boundary Condition	93
7.5	Boltzmann–Matano Analysis	93
<b>8</b>	<b>Stefan Problems</b>	<b>97</b>
8.1	Steady-State Solutions to the Diffusion Equation	97
8.2	Deal–Grove Analysis	100
8.3	Diffusion-Controlled Growth of a Spherical Precipitate	102
8.4	Diffusion-Limited Growth in Cylindrical Coordinates	105
<b>9</b>	<b>Phase Transformations</b>	<b>109</b>
9.1	Transformation-Rate-Limited Growth	109
9.2	Diffusion-Limited Growth	111
9.3	Thermally Limited Growth	111
9.4	Casting of Metals	113
9.5	Operating Point	114
<b>10</b>	<b>Crystal Growth Methods</b>	<b>117</b>
10.1	Melt Growth	117
10.1.1	Czochralski Growth	117
10.1.2	Floating Zone	121
10.1.3	Bridgman Method	123
10.1.4	Chalmers Method	123
10.1.5	Horizontal Gradient Freeze	124
10.2	Solution Growth	124
10.2.1	Growth from Aqueous Solutions	125
10.2.2	Flux Growth	125
10.2.3	Hydrothermal Growth	125
10.3	Vapor-Phase Growth	126
10.4	Stoichiometry	126
<b>11</b>	<b>Segregation</b>	<b>129</b>
11.1	Segregation during a Phase Change	129
11.2	Lever Rule	130
11.3	Scheil Equation	131
11.4	Zone Refining	133
11.5	Diffusion at a Moving Interface	134
11.5.1	Steady-state Diffusion at a Moving Interface	134
11.5.2	Initial and Final Transients	137
11.6	Segregation in Three Dimensions	139
11.7	Burton, Primm and Schlichter Analysis	139

<b>12</b>	<b>Interface Instabilities</b>	143
12.1	Constitutional Supercooling	143
12.2	Mullins and Sekerka Linear Instability Analysis	149
12.3	Anisotropic Interface Kinetics	152
<b>13</b>	<b>Chemical Reaction Rate Theory</b>	155
13.1	The Equilibrium Constant	155
13.2	Reaction Rate Theory	155
13.3	Reaction Rate Constant	157
13.4	Transition State Theory	157
13.5	Experimental Determination of the Order of a Reaction	158
13.6	Net Rate of Reaction	160
13.7	Catalysis	162
13.8	Quasi-Equilibrium Model for the Rate of a First-Order phase Change	163
<b>14</b>	<b>Phase Equilibria</b>	165
14.1	First-Order Phase Changes	165
14.2	Second-Order Phase Changes	169
14.3	Critical Point between Liquid and Vapor	172
<b>15</b>	<b>Nucleation</b>	175
15.1	Homogeneous Nucleation	175
15.1.1	Volmer Analysis	176
15.1.2	Turnbull's Droplet Experiment	179
15.1.3	Surface Free Energy	181
15.1.4	Becker–Döring Analysis	183
15.1.5	Nucleation Rate	187
15.1.6	Limitations of the Becker–Döring Analysis	188
15.1.7	Assumptions in the Classical Nucleation Theory	188
15.1.8	Nucleation of a Precipitate Particle	189
15.2	Heterogeneous Nucleation	190
15.2.1	Heterogeneous Nucleation Theory	191
15.2.2	Nucleation Lore	192
15.2.3	Cavitation	193
15.2.4	Re-entrant Cavities	194
15.2.5	Cloud Seeding	195
15.2.6	Industrial Crystallization	195
15.2.7	Grain Refiners	196
15.2.8	Residues	196
15.3	Johnson–Mehl–Avrami Equation	197
15.3.1	Johnson–Mehl Equation	197
15.3.2	Johnson–Mehl–Avrami	199
<b>16</b>	<b>Surface Layers</b>	203
16.1.1	Langmuir Adsorption	203
16.1.2	CVD Growth by a Surface-Decomposition Reaction	204

16.1.3	Langmuir–Hinshelwood Reaction	205
16.2	Surface Nucleation	206
16.2.1	Nucleation on a Surface during Vapor Deposition	206
16.2.2	Cluster Formation	207
16.2.3	Rate Equations	209
16.3	Thin Films	210
16.3.1	Epitaxy	210
16.3.2	Deposited Surface Layers	212
16.4	Surface Reconstruction	213
16.5	Amorphous Deposits	214
16.6	Surface Modification	217
16.7	Fractal Deposits	217
16.8	Strain Energy and Misfit Dislocations	219
16.9	Strained-Layer Growth	223
16.9.1	Surface Modulation	223
16.9.2	Strained-Layer Superlattice	223
16.9.3	Graded-Strain Layers	224
<b>17</b>	<b>Thin-Film Deposition</b>	227
17.1	Liquid Phase Epitaxy	227
17.2	Growth Configurations for LPE	228
17.3	Chemical Vapor Deposition	229
17.4	Metal-Organic Chemical Vapor Deposition	233
17.5	Physical Vapor Deposition	234
17.6	Sputter Deposition	235
17.7	Metallization	235
17.8	Laser Ablation	236
17.9	Molecular Beam Epitaxy	237
17.10	Atomic Layer Epitaxy	238
<b>18</b>	<b>Plasmas</b>	241
18.1	Direct Current (DC) Plasmas	241
18.2	Radio-Frequency Plasmas	243
18.3	Plasma Etching	245
18.4	Plasma Reactors	247
18.5	Magnetron Sputtering	249
18.6	Electron Cyclotron Resonance	251
18.7	Ion Milling	252
<b>19</b>	<b>Rapid Thermal Processing</b>	253
19.1	Rapid Thermal Processing	253
19.2	Rapid Thermal Processing Equipment	254
19.3	Radiative Heating	254
19.4	Temperature Measurement	256
19.5	Thermal Stress	257
19.6	Laser Heating	258

<b>20</b>	<b>Kinetics of First-Order Phase Transformations</b>	259
20.1	General Considerations	259
20.2	The Macroscopic Shape of Crystals	261
20.3	General Equation for the Growth Rate of Crystals	262
20.4	Kinetic Driving Force	263
20.5	Vapor-Phase Growth	264
20.5.1	Equilibrium	264
20.5.2	Kinetics of Vapor-Phase Growth	265
20.6	Melt Growth	267
20.6.1	Early Models for Melt Growth	268
20.6.2	Melt Growth Rates	269
20.7	Molecular Dynamics Studies of Melt Crystallization Kinetics	269
20.8	The Kossel–Stranski Model	272
20.9	Nucleation of Layers	273
20.10	Growth on Screw Dislocations	275
20.11	The Fluctuation Dissipation Theorem	277
20.11.1	Determination of the Kinetic Coefficient	277
20.11.2	Experimental Determination of Surface Tension	281
<b>21</b>	<b>The Surface-Roughening Transition</b>	283
21.1	Surface Roughness	283
21.2	The Ising Model	284
21.3	Cooperative Processes	285
21.4	Monte Carlo Simulations of Crystallization	287
21.5	Equilibrium Surface Structure	288
21.5.1	Thermodynamic Model for Surface Roughness	288
21.5.2	Application of Surface Roughening to Materials	291
21.5.3	Snow Flakes	294
21.5.4	Rate-Theory Analysis of Surface Roughness	295
21.5.5	Surface Roughness in the Ising Model	297
21.6	Computer Simulations	298
21.6.1	Determination of the Kinetic Coefficient	301
21.6.2	Simulations of Silicon Growth	302
21.7	Growth Morphologies	304
21.8	Kinetic Roughening	306
21.9	Polymer Crystallization	308
<b>22</b>	<b>Alloys: Thermodynamics and Kinetics</b>	311
22.1	Crystallization of Alloys	311
22.2	Phase Equilibria	313
22.3	Regular Solution Model	314
22.4	Near-Equilibrium Conditions	316
22.5	Phase Diagrams	317
22.6	The DLP Model	320

<b>23</b>	<b>Phase Separation</b>	323
23.1	Ordering versus Phase Separation	323
23.2	Phase Separation	324
23.3	Analytical Model for Spinodal Decomposition	326
23.4	Microstructure Resulting from Phase Separation	328
<b>24</b>	<b>Non-Equilibrium Crystallization of Alloys</b>	331
24.1	Non-Equilibrium Crystallization	331
24.2	Experiment	331
24.3	Computer Modeling	333
24.4	Analytical Model	335
24.5	Comparison with Experiment	336
24.6	Crystallization of Glasses	338
<b>25</b>	<b>Coarsening, Ripening</b>	341
25.1	Coarsening	341
25.2	Free Energy of a Small Particle	341
25.3	Coarsening in a Solution	342
25.4	Coarsening of Dendritic Structures	344
25.5	Sintering	345
25.6	Bubbles	346
25.7	Grain Boundaries	347
25.8	Scratch Smoothing	348
<b>26</b>	<b>Dendrites</b>	351
26.1	Dendritic Growth	351
26.2	Conditions for Dendritic Growth	351
26.3	Simple Dendrite Model	353
26.4	Phase Field Modeling	358
26.5	Faceted Growth	358
26.6	Distribution Coefficient	358
<b>27</b>	<b>Eutectics</b>	361
27.1	Eutectic Phase Diagram	361
27.2	Classes of Eutectic Microstructures	362
27.2.1	Class I Eutectics	362
27.2.2	Class II Eutectics	365
27.2.3	Class III Eutectics	367
27.3	Analysis of Lamellar Eutectics	367
27.3.1	Curvature of the Interface	368
27.3.2	Diffusion	370
27.3.3	Calculation of Eutectic Interface Shape	372
27.4	Off-Composition Eutectics	373
27.5	Coupled Growth	374
27.6	Third-Component Elements	378

- 28**      **Castings**    381  
28.1     Grain Structure of Castings    381  
28.2     Dendrite Remelting    382

**Subject Index by Page**    387

**Subject Index by Chapter Sections**    403